

SOT23 PNP SILICON PLANAR DARLINGTON TRANSISTOR

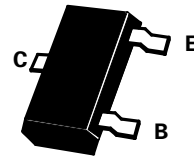
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FMMTA64

PARTMARKING DETAIL – FMMTA64 - Z2V

COMPLEMENTARY TYPES – FMMTA64 - FMMTA14



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-10	V
Peak Pulse Current	I_{CM}	-800	mA
Continuous Collector Current	I_C	-500	mA
Peak Base Current	I_{BM}	-200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	FMMTA64		UNIT	CONDITIONS.
		MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-30		V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30		V	$I_C = -10mA, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-10		V	$I_E = -10\mu A, I_C = 0$
Collector Cut-Off Current	I_{CBO}		-0.1	μA	$V_{CB} = -30V, I_E = 0$
Emitter Cut-Off Current	I_{EBO}		-0.1	μA	$V_{CE} = -10V$
Static Forward Current Transfer Ratio	h_{FE}	10K 20K			$I_C = -10mA, V_{CE} = 5V^*$ $I_C = -100mA, V_{CE} = 5V^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-1.5	V	$I_C = -100mA, I_B = -0.1mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-2.0	V	$I_C = -100mA, I_B = -0.1mA^*$
Transition Frequency	f_T	125		MHz	$I_C = -50mA, V_{CE} = -5V$ $f = 20MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

For typical characteristics graphs see FZTA64 datasheet.

